Single 2-Input NOR Gate with Open Drain Output

NLV74VHC1G03, NLV74VHC1GT03

The NLV74VHC1G03 / NLV74VHC1GT03 is a 2-input NOR Gate with an open drain output in tiny footprint packages.

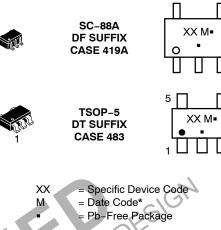
The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when $V_{CC} = 0$ V and when the output voltage exceeds V_{CC} . These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- $\bullet\,$ Designed for 2.0 V to 5.5 V V_{CC} Operation
- 3.5 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- IOFF Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A and TSOP-5 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Figure 1. Logic Symbol

MARKING DIAGRAMS



(Note: Microdot may be in either location) Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 8 of this data sheet.

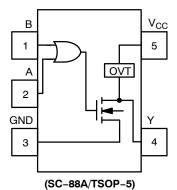
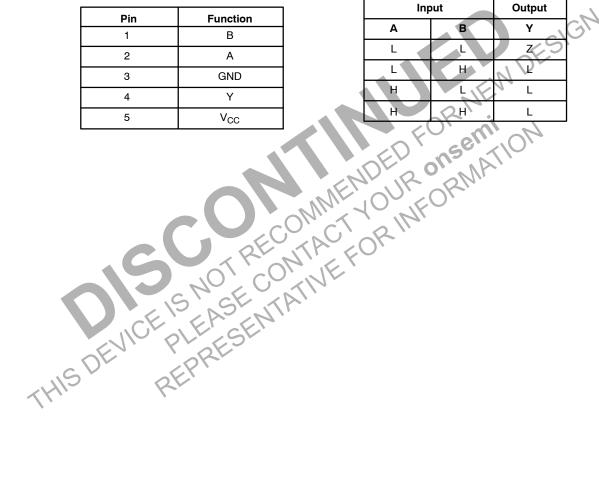


Figure 2. Pinout (Top View)

PIN ASSIGNMENT

(SC-88A/TSOP-5)

FUNCTION TABLE



MAXIMUM RATINGS

| Symbol | C | Value | Unit | |
|-------------------------------------|---------------------------------|---|--|------|
| V _{CC} | DC Supply Voltage | -0.5 to +7.0 | V | |
| V _{IN} | DC Input Voltage | -0.5 to +7.0 | V | |
| V _{OUT} | DC Output Voltage | 1Gxx | –0.5 to V _{CC} + 0.5 | V |
| | | 1GTxx Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V) | $\begin{array}{c} -0.5 \text{ to } V_{CC} + 0.5 \\ -0.5 \text{ to } +7.0 \\ -0.5 \text{ to } +7.0 \end{array}$ | |
| Ι _{ΙΚ} | DC Input Diode Current | V _{IN} < GND | -20 | mA |
| I _{OK} | DC Output Diode Current | 1Gxx $V_{OUT} > V_{CC}, V_{OUT} < GND$ | ±20 | mA |
| | | 1GTxx V _{OUT} < GND | -20 | |
| I _{OUT} | DC Output Source/Sink Current | ±25 | mA | |
| I _{CC} or I _{GND} | DC Supply Current per Supply Pi | ±50 | mA | |
| T _{STG} | Storage Temperature Range | -65 to +150 | ∕ °C | |
| ΤL | Lead Temperature, 1 mm from Ca | 260 | °C | |
| TJ | Junction Temperature Under Bias | | +150 | °C |
| θ_{JA} | Thermal Resistance (Note 2) | SC-88A TSOP-5 | 377 320 | °C/W |
| P _D | Power Dissipation in Still Air | 332 390 | mW | |
| MSL | Moisture Sensitivity | Level 1 | - | |
| F _R | Flammability Rating | Oxygen Index: 28 to 34 | UL 94 V-0 @ 0.125 in | _ |
| V_{ESD} | ESD Withstand Voltage (Note 3) | Human Body Model Charged Device Model | 2000 1000 | V |
| I _{Latchup} | Latchup Performance (Note 4) | | ±100 | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Applicable to devices with outputs that may be tri-stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A. THIS DEVICES IL REPRESENT
- 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

| Symbol | C | Min | Max | Unit | |
|---------------------------------|-----------------------------|---|-------------|-------------------------------|------|
| V _{CC} | Positive DC Supply Voltage | 2.0 | 5.5 | V | |
| V _{IN} | DC Input Voltage | 0 | 5.5 | V | |
| V _{OUT} | DC Output Voltage | 1Gxx | 0 | V _{CC} | V |
| | | 1GTxx Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V) | 0 0 0 | V _{CC} 5.5 5.5 | |
| T _A | Operating Temperature Range | -55 | +125 | °C | |
| t _r , t _f | Input Rise and Fall Time | V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V | 0 0 | 100 20 | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (NLV74VHC1G03)

| | | Test | V _{cc} | T _A = 25°C | | $-40^{\circ}C \leq T_{A} \leq 85^{\circ}C \qquad -55^{\circ}C \leq T_{A} \leq$ | | | A ≤ 125°C | | |
|------------------|-----------------------------------|---|-----------------|-----------------------|------|--|------|--------------|-----------|--------------|------|
| Symbol | Parameter | Conditions | (V) | Min | Тур | Max | Min | Max | Min | Max | Unit |
| VIH | High-Level Input Voltage | | 2.0 | 1.5 | - | | 1.5 | | 1.5 | - | V |
| | vollage | | 3.0 | 2.1 | - | - | 2.1 | 24 | 2.1 | - | |
| | | | 4.5 | 3.15 | | - | 3.15 | - () | 3.15 | - | 1 |
| | | | 5.5 | 3.85 | - | - | 3.85 | Seix | 3.85 | - | |
| V _{IL} | Low-Level Input | | 2.0 | - | - | 0.5 | 0 | 0.5 | - | 0.5 | V |
| | Voltage | | 3.0 | | . 16 | 0.9 | SE.C | 0.9 | - | 0.9 | |
| | | | 4.5 | 1- 1 | VL. | 1.35 | Ht. | 1.35 | - | 1.35 | 1 |
| | | | 5.5 | $\gamma \mathcal{O}$ | 5 | 1.65 | | 1.65 | - | 1.65 | |
| V _{OL} | Low-Level Output Voltage | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu A$ | 2.0 | N | 0.0 | 0.1 | _ | 0.1 | _ | 0.1 | V |
| | Vollage | loι = 50 μA | 3,0 | DZ. | 0.0 | 0.1 | _ | 0.1 | _ | 0.1 | |
| | | I _{OL} = 50 μA | 4.5 | 1 | 0.0 | 0.1 | - | 0.1 | - | 0.1 | |
| | | $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$ | 3.0 4.5 | ζĘ. | - | 0.36 0.36 | _ | 0.44 0.44 | - | 0.52 0.52 | |
| I _{IN} | Input Leakage Current | V _{IN} = 5.5 V or GND | 2.0 to 5.5 | - | - | ±0.1 | - | ±1.0 | - | ±1.0 | μA |
| I _{OZ} | 3–State Output Leakage Current | V _{OUT} = 0 V to 5,5 V | 5.5 | - | - | ±0.25 | - | ±2.5 | - | ±2.5 | μΑ |
| I _{OFF} | Power Off Leakage Current | V _{IN} = 5.5 V | 0.0 | - | - | 1.0 | - | 10 | - | 10 | μA |
| I _{CC} | Quiescent Supply Current | V _{IN} = V _{CC} or GND | 5.5 | - | - | 1.0 | - | 20 | - | 40 | μA |

DC ELECTRICAL CHARACTERISTICS (NLV74VHC1GT03)

| | | Test Conditions | V _{CC} | T _A = 25°C | | С | -40°C ≤ 1 | Γ _A ≤ 85°C | -55°C ≤ T | A ≤ 125°C | |
|------------------|--|--|---------------------------------|-----------------------|-----------------------------|----------------------------|------------------|----------------------------|------------------|-----------------------------------|------|
| Symbol | Parameter | | VCC (V) | Min | Тур | Max | Min | Max | Min | Max | Unit |
| V _{IH} | High-Level Input | | 2.0 | 1.0 | - | - | 1.0 | - | 1.0 | - | V |
| | Voltage | | 3.0 | 1.4 | - | - | 1.4 | - | 1.4 | - | |
| | | | 4.5 | 2.0 | - | - | 2.0 | - | 2.0 | - | |
| | | | 5.5 | 2.0 | - | - | 2.0 | - | 2.0 | - | |
| V _{IL} | Low-Level Input | | 2.0 | 1 | - | 0.28 | - | 0.28 | - | 0.28 | V |
| | Voltage | | 3.0 | 1 | 1 | 0.45 | - | 0.45 | - | 0.45 | |
| | | | 4.5 | 1 | 1 | 0.8 | - | 0.8 | - | 0.8 | |
| | | | 5.5 | 1 | 1 | 0.8 | - | 0.8 | - | 0.8 | |
| V _{OL} | Low-Level Output Voltage | | 2.0 3.0 4.5 3.0 4.5 | | 0.0 0.0 0.0 - - | 0.1 0.1 0.36 0.36 | | 0.1 0.1 0.44 0.44 | - - - - | 0.1 0.1 0.5 0.52 0.52 | V |
| I _{IN} | Input Leakage Cur- rent | V _{IN} = 5.5 V or GND | 2.0 to 5.5 | - | - | ±0.1 | 1 | ±1.0 | NV | ±1.0 | μΑ |
| I _{OZ} | 3-State Output Leakage Current | V _{OUT} = 0 V to 5.5 V | 5.5 | - | - | ±0.25 | | ±2.5 | - | ±2.5 | μΑ |
| I _{OFF} | Power Off Leakage Current | V _{IN} = 5.5 V or V _{OUT} = 5.5 V | 0 | | - | 1.0 | D | 510 | 1014 | 10 | μΑ |
| I _{CC} | Quiescent Supply Current | V _{IN} = V _{CC} or GND | 5.5 | | | 7.0 | R | 20 | - | 40 | μΑ |
| I _{CCT} | Increase in Quies- cent Supply Current per Input Pin | One Input: V _{IN} = 3.4 V; Other Input at V _{CC} or GND | 5.5 | | AC | 1.85 | MFC | 1.5 | - | 1.65 | mA |

THIS DEVICE PLEASENTATIVE REPRESENTATIVE

AC ELECTRICAL CHARACTERISTICS

| | | | | T _A = 25°C | | $-40^\circ C \leq T_A \leq 85^\circ C$ | | $-55^\circ C \leq T_A \leq 125^\circ C$ | | | |
|------------------|---|---|---------------------|-----------------------|-----|--|-----|---|-------------------------------------|----------------------|------|
| Symbol | Parameter | Conditions | V _{CC} (V) | Min | Тур | Max | Min | Max | Min | Max | Unit |
| t _{PZL} | Propagation Delay, | C _L = 15 pF | 3.0 to 3.6 | - | 5.6 | 7.9 | - | 9.5 | - | 11.0 | ns |
| | (A or B) to Y (Figures 3 and 4) | C _L = 50 pF | | - | 8.1 | 11.4 | - | 13.0 | - | 15.5 | |
| | | C _L = 15 pF | 4.5 to 5.5 | - | 3.6 | 5.5 | - | 6.5 | - | 8.0 | |
| | | C _L = 50 pF | | - | 5.1 | 7.5 | - | 8.5 | - | 10.0 | |
| t _{PLZ} | PLZ (A or B) to Y (Figures 3 and 4) | C _L = 15 pF | 3.0 to 3.6 | - | 6.5 | 9.7 | - | 11.5 | - | 14.5 | ns |
| | | C _L = 50 pF | | - | 8.1 | 11.4 | - | 13.0 | _ | 15.5 | |
| | | C _L = 15 pF | 4.5 to 5.5 | - | 4.8 | 6.8 | - | 8.0 | _ | 10.0 | |
| | | C _L = 50 pF | | - | 5.1 | 7.5 | - | 8.5 | _ | 10.0 | |
| C _{IN} | Input Capacitance | | | - | 4.0 | 10 | - | 10 | - | 10 | pF |
| C _{OUT} | Output Capacitance | Output in High Impedance State | | - | 6.0 | - | - | | - | SIGN | pF |
| C _{PD} | Power Dissipation Ca | pacitance (Not | e 5) | | | | | Typical | @ 25°C, V_C 8.0 | _C = 5.0 V | pF |

5. Cp_D is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = Cp_D • V_{CC} • f_{In} + I_{CC}. Cp_D is used to determine the no-load dynamic power consumption; P_D = Cp_D • V_{CC}² • f_{In} + I_{CC} • V_{CC}.

 R_L, Ω

Х

1 k

1 k

 V_{CC}

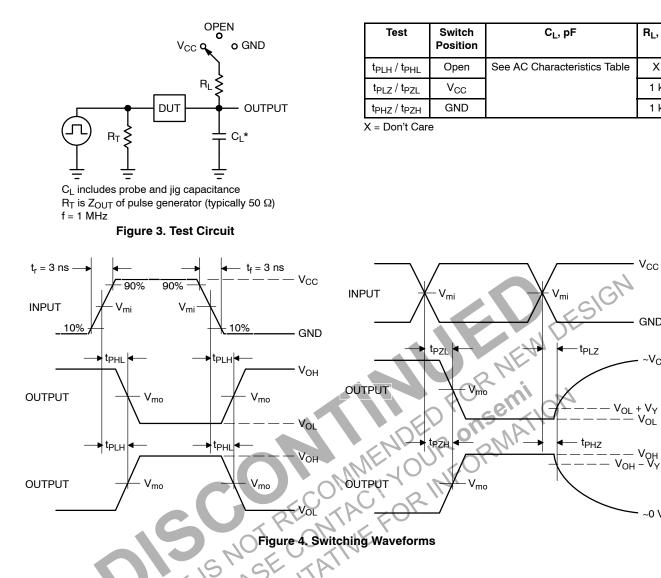
GND

 $\sim V_{CC}$

VY

V_{OL}

- ~0 V



| | NCE E GE | V _m | V _{mo} , V | | |
|---------------------|---------------------|-------------------------------------|---|--------------------|--|
| V _{CC} , V | V _{mi} , V | t _{PLH} , t _{PHL} | t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ} | V _Y , V | |
| 3.0 to 3.6 | V _{CC} /2 | V _{CC} /2 | V _{CC} /2 | 0.3 | |
| 4.5 to 5.5 | V _{CC} /2 | V _{CC} /2 | V _{CC} /2 | 0.3 | |

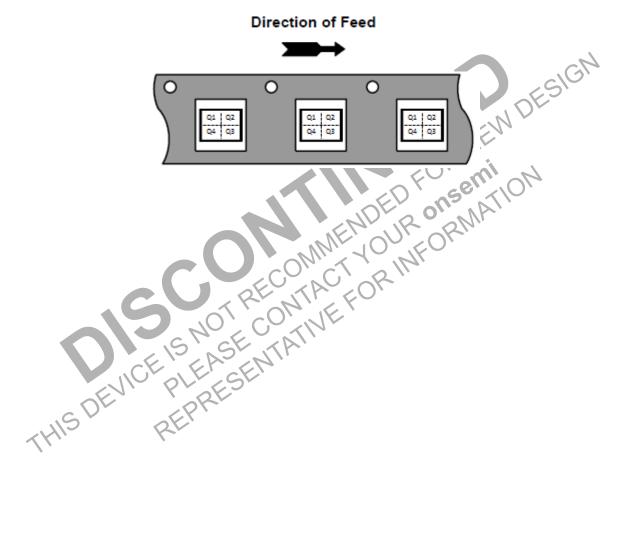
ORDERING INFORMATION

| Device | Packages | Specific Device Code | Pin 1 Orientation (See below) | Shipping [†] |
|-------------------------|----------|----------------------|----------------------------------|-----------------------|
| MC74VHC1G03DFT2G-L22038 | SC-88A | VP | Q4 | 3000 / Tape & Reel |
| NLVVHC1G03DFT1G* | SC-88A | VP | Q2 | 3000 / Tape & Reel |
| MC74VHC1G03DTT1G | TSOP-5 | VP | Q4 | 3000 / Tape & Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL



NSEM



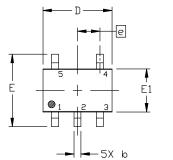
SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE M**

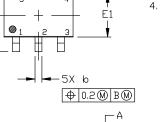
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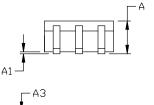
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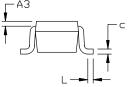
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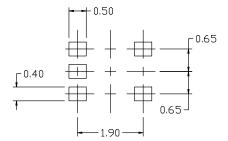
DATE 11 APR 2023











RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

| DIM | MILLIMETERS | | | | | | |
|-----|-------------|----------|------|--|--|--|--|
| MIU | MIN, | NDM. | MAX. | | | | |
| A | 0.80 | 0.95 | 1.10 | | | | |
| A1 | | | 0.10 | | | | |
| A3 | 0.20 REF | | | | | | |
| b | 0.10 | 0.20 | 0.30 | | | | |
| С | 0.10 | | 0.25 | | | | |
| D | 1.80 | 2.00 | 5'50 | | | | |
| E | 2.00 | 2.10 | 5'50 | | | | |
| E1 | E1 1.15 | | 1,35 | | | | |
| e | | 0.65 BSI | С | | | | |
| L | 0.10 | 0.15 | 0.30 | | | | |

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,

PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,

OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

CONTROLLING DIMENSION: MILLIMETERS 419A-01 DBSOLETE, NEW STANDARD 419A-02

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

Μ = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

| STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR | STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE | STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1 | STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2 | STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4 | E |
|--|--|--|--|--|---|
| STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE | STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR | STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER | STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE | Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p | ype is not called efer to the device |
| DOCUMENT NUMBER: | 98ASB42984B | | | ot when accessed directly from when stamped "CONTROLLED (| |
| DESCRIPTION: | SC-88A (SC-70- | 5/SOT-353) | | | PAGE 1 OF 1 |
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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

TSOP-5 3.00x1.50x0.95, 0.95P **CASE 483** ISSUE P DATE 01 APR 2024 NOTES: 5X b 0.20 C A B DIMENSIONING AND TOLERANCING CONFORM TO ASME NOTE 5 1. Y14.5-2018. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES). MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. 2. В 3. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. Ė1 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D. 5 OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS PIN 1 ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND IDENTIFIER MORE THAN 0.2 FROM BODY. le A MILLIMETERS DIM NOM. TOP VIEW MIN. MAX 0.900 1.000 1.100 DETAIL A А (A2) A1 0.010 0.055 0.100 Α2 0.950 REF 0.250 0.375 0.500 h 0.100 0.180 0.260 с 0.05 C SEATING 2.850 D 3.000 3.150 Ċ A1 PLANE END VIEW SIDE VIEW Ε 2.500 2.750 3.000 1.350 E1 1.500 1.650 0.950 BSC е 0.250 GAUGE 0.400 L 0.200 0.600 0° 5° 10° Θ 1.900Ð 0.950 "A DETAIL SCALE 2:1 GENERIC **MARKING DIAGRAM*** 2.400 5 5 XXXAYW= XXX M= 1.000 1 0.700Analog Discrete/Logic RECOMMENDED MOUNTING FOOTPRINT* XXX = Specific Device Code XXX = Specific Device Code FOR ADDITIONAL INFORMATION ON OUR Pb-FREE А = Assembly Location Μ = Date Code STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD = Pb-Free Package v = Year THE ON SEMICONDUCTOR SOLDERING AND MOUNTING W = Work Week TECHNIQUES REFERENCE MANUAL, SOLDERRM/D. = Pb-Free Package (Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking. Electronic versions are uncontrolled except when accessed directly from the Document Repository. DOCUMENT NUMBER: 98ARB18753C Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** TSOP-5 3.00x1.50x0.95, 0.95P PAGE 1 OF 1 onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

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